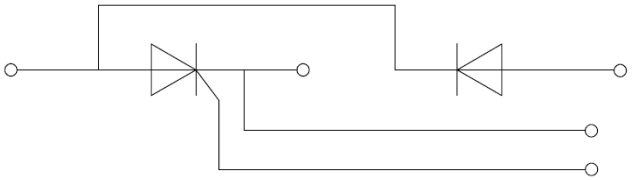
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FIG.1: Power dissipation vs. on-state current (per thyristor or diode)

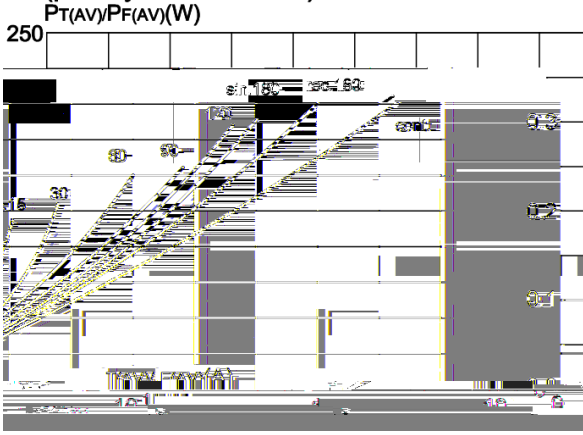


FIG.2: Maximum transient thermal impedance junction to case(per thyristor or diode)

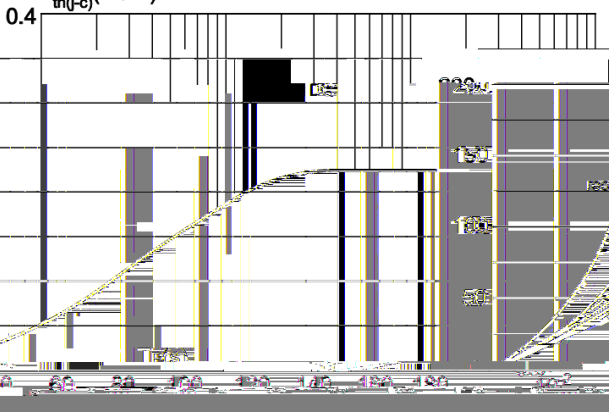


FIG.3: Forward characteristics

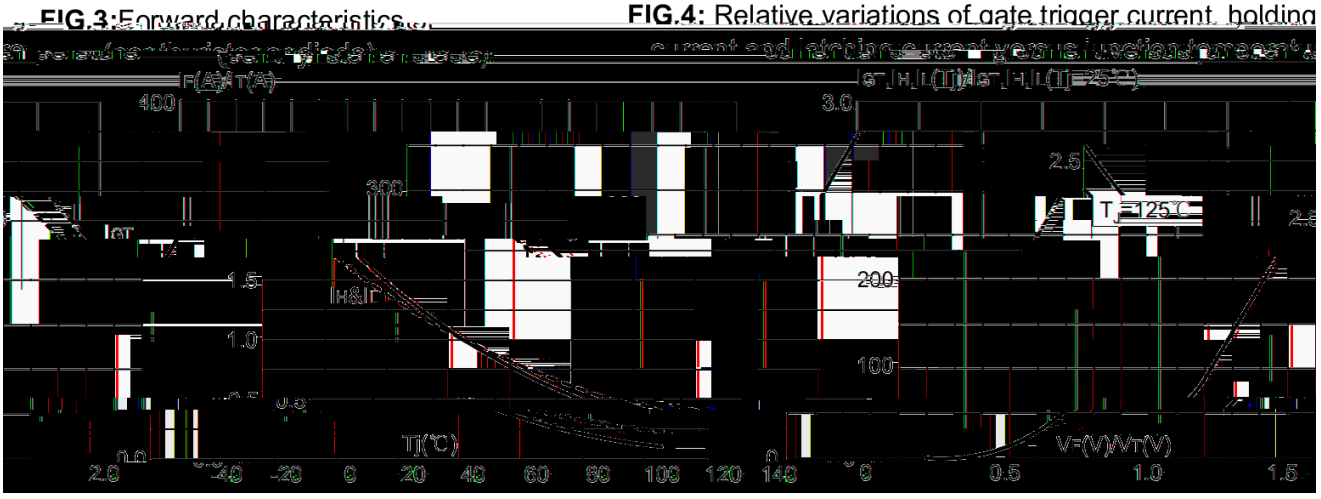


FIG.4: Relative variations of gate trigger current, holding

FIG.5 Gate trigger characteristics

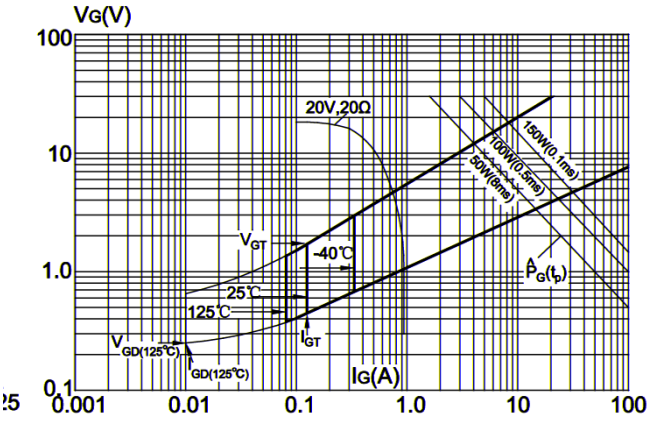
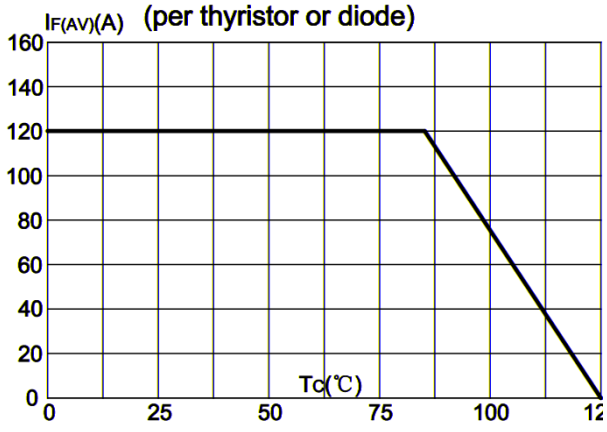
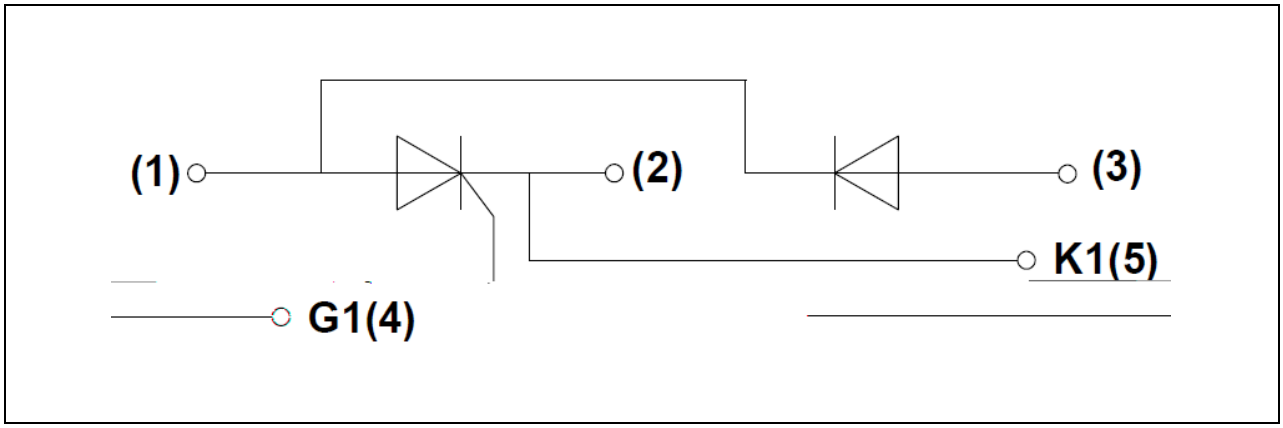
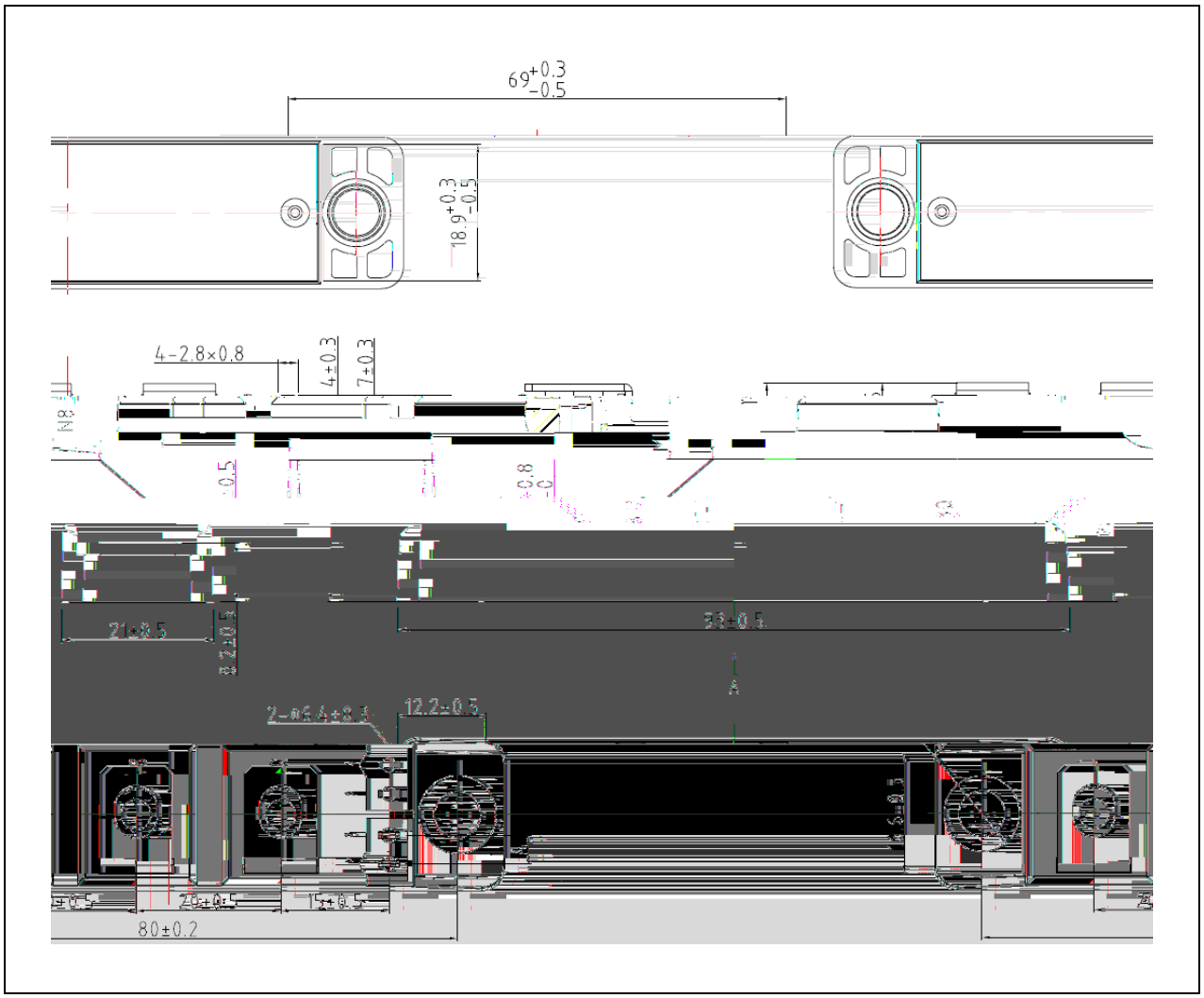


FIG.6: Forward current vs. case temperature (per thyristor or diode)




(1)
(2)
(3)
K1(5)
G1(4)


69+0.3 -0.5
18.9+0.3 -0.5
4-2.8×0.8
4±0.3
7±0.3
21±0.5
33±0.5
12.2±0.3
80±0.2